Octal Bus Buffer

With 5V-Tolerant Inputs

The MC74LVX244 is an advanced high speed CMOS non–inverting 3–state octal bus buffer and has two active low output enables. It is also designed to work with 3–state memory address drivers, etc. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

- High Speed: $t_{PD} = 4.7 \text{ ns (Typ)}$ at $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A \text{ (Max)}$ at $T_A = 25 \text{°C}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Low Noise: $V_{OLP} = 0.8 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:

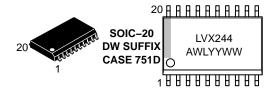
Human Body Model > 2000 V; Machine Model > 200 V

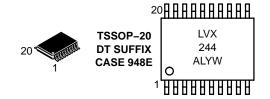
• Pb-Free Packages are Available*

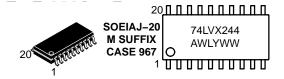


http://onsemi.com

MARKING DIAGRAMS







A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

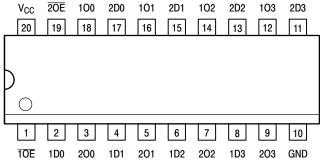


Figure 1. 20-Lead Pinout (Top View)

PIN NAMES

Pins	Function
nOE	Output Enable Inputs
1Dn, 2Dn	Data Inputs
1On, 2On	3-State Outputs

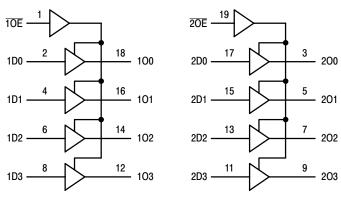


Figure 2. Logic Diagram

FUNCTION TABLE

INP	JTS	OUTPUTS
10E, 20E	1Dn, 2Dn	10n, 20n
L	L	L
L	Н	Н
Н	X	Z

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74LVX244DWR2	SOIC-20	1000 Tape & Reel
MC74LVX244DWR2G	SOIC-20 (Pb-Free)	1000 Tape & Reel
MC74LVX244DT	TSSOP-20*	50 Units / Rail
MC74LVX244DTR2	TSSOP-20*	2500 Tape & Reel
MC74LVX244M	SOEIAJ-20	50 Units / Rail
MC74LVX244MEL	SOEIAJ-20	2000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}This package is inherently Pb-Free.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
V _{in}	DC Input Voltage	-0.5 to +7.0	V
V _{out}	DC Output Voltage	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Diode Current	-20	mA
I _{OK}	Output Diode Current	±20	mA
l _{out}	DC Output Current, per Pin	±25	mA
Icc	DC Supply Current, V _{CC} and GND Pins	±75	mA
P _D	Power Dissipation	180	mW
T _{stg}	Storage Temperature	-65 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	3.6	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	-40	+85	°C
Δt/ΔV	Input Rise and Fall Time	0	100	ns/V

DC ELECTRICAL CHARACTERISTICS

			v _{cc}	Т	_A = 25°	С	$T_A = -40$) to 85°C	
Symbol	Parameter	Test Conditions		Min	Тур	Max	Min	Max	Unit
V _{IH}	High-Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4			1.5 2.0 2.4		V
V _{IL}	Low-Level Input Voltage		2.0 3.0 3.6			0.5 0.8 0.8		0.5 0.8 0.8	V
V _{OH}	High-Level Output Voltage (V _{in} = V _{IH} or V _{IL})	$I_{OH} = -50\mu A$ $I_{OH} = -50\mu A$ $I_{OH} = -4mA$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V _{OL}	Low-Level Output Voltage (V _{in} = V _{IH} or V _{IL})	$I_{OL} = 50\mu A$ $I_{OL} = 50\mu A$ $I_{OL} = 4mA$	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
l _{in}	Input Leakage Current	V _{in} = 5.5V or GND	3.6			±0.1		±1.0	μΑ
l _{OZ}	Maximum 3–State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	3.6			±0.2 5		±2.5	μΑ
I _{CC}	Quiescent Supply Current	V _{in} = V _{CC} or GND	3.6			4.0		40.0	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$)

				Т	A = 25°	С	$T_A = -40$) to 85°C	
Symbol	Parameter	Test Cond	ditions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Propagation Delay Input to Output	V _{CC} = 2.7V	$C_L = 15pF$ $C_L = 50pF$		6.1 8.6	11.4 14.9	1.0 1.0	13.5 17.0	ns
		$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15pF$ $C_L = 50pF$		4.7 7.2	7.1 10.6	1.0 1.0	8.5 12.0	
t _{PZL} , t _{PZH}	Output Enable Time to High and Low Level	$V_{CC} = 2.7V$ $R_L = 1k\Omega$	$C_L = 15pF$ $C_L = 50pF$		7.1 9.6	13.8 17.3	1.0 1.0	16.5 20.0	ns
		$V_{CC} = 3.3 \pm 0.3V$ $R_L = 1k\Omega$	$C_L = 15pF$ $C_L = 50pF$		5.5 8.0	8.8 12.3	1.0 1.0	10.5 14.0	
t _{PLZ} , t _{PHZ}	Output Disable Time From High and Low Level	$V_{CC} = 2.7V$ $R_L = 1k\Omega$	C _L = 50pF		11.6	16.0	1.0	19.0	ns
		$V_{CC} = 3.3 \pm 0.3V$ $R_L = 1k\Omega$	C _L = 50pF		9.7	11.4	1.0	13.0	
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 1)	$V_{CC} = 2.7V$ $V_{CC} = 3.3 \pm 0.3V$	$C_L = 50pF$ $C_L = 50pF$			1.5 1.5		1.5 1.5	ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

CAPACITIVE CHARACTERISTICS

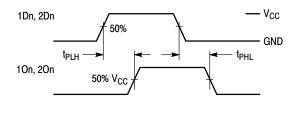
		T _A = 25°C		T _A = - 40 to 85°C			
Symbol	Parameter	Min	Тур	Max	Min	Max	Unit
Cin	Input Capacitance		4	10		10	pF
C _{out}	Maximum Three-State Output Capacitance		6				pF
C _{PD}	Power Dissipation Capacitance (Note 2)		19				pF

C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per bit). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 3.3$ V, Measured in SOIC Package)

		T _A =	25°C	
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.5	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.5	-0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

SWITCHING WAVEFORMS



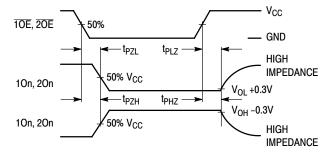
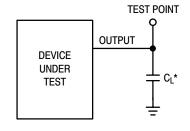


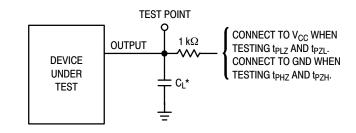
Figure 3.

Figure 4.

TEST CIRCUITS



*Includes all probe and jig capacitance



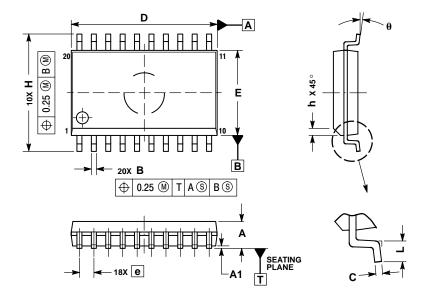
*Includes all probe and jig capacitance

Figure 5. Propagation Delay Test Circuit

Figure 6. Three-State Test Circuit

PACKAGE DIMENSIONS

SOIC-20 **DW SUFFIX** CASE 751D-05 ISSUE G

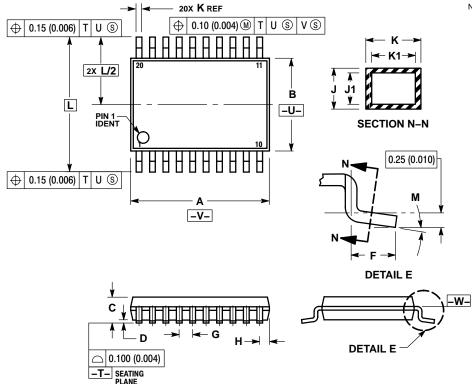


NOTES:

- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES
 PER ASME Y14.5M, 1994.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
- PROTRUSION: MAXIMUM MOLD PROTRUSION 0.15 PER SIDE. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
В	0.35	0.49			
С	0.23	0.32			
D	12.65	12.95			
E	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50	0.90			
θ	0 °	7 °			

TSSOP-20 **DT SUFFIX** CASE 948E-02 **ISSUE B**



NOTES:

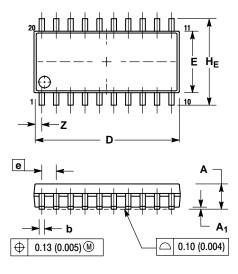
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION:
 MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE
 MOLD FLASH, PROTRUSIONS OR GATE
 BURRS. MOLD FLASH OR GATE BURRS
 SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION.
 SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE
- DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 DAMBAR FOR THOSING STALL BOOM (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. 3. TERMINAL NUMBERS ARE SHOWN
- FOR REFERENCE ONLY.

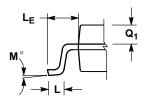
 7. DIMENSION A AND B ARE TO BE
 DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
Ĺ	6.40	BSC	0.252 BSC		
M	0°	8°	0°	8°	

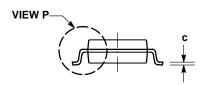
PACKAGE DIMENSIONS

SOEIAJ-20 **M SUFFIX** CASE 967-01 **ISSUE O**





DETAIL P



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
 - Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- CONTROLLING DIMENSION. MILLIME I ER.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD
 FLASH OR PROTRUSIONS AND ARE MEASURED
 AT THE PARTING LINE. MOLD FLASH OR
 PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
- PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
 PER SIDE.

 4. TERMINAL NUMBERS ARE SHOWN FOR
 REFERENCE ONLY.

 5. THE LEAD WIDTH DIMENSION (b) DOES NOT
 INCLUDE DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
 TOTAL IN EXCESS OF THE LEAD WIDTH
 DIMENSION AT MAXIMUM MATERIAL CONDITION.
 DAMBAR CANNOT BE LOCATED ON THE LOWER
 RADILIS OR THE FOOT. MINIMUM SPACE RADIUS OR THE FOOT. MINIMUM SPACE
 BETWEEN PROTRUSIONS AND ADJACENT LEAD
 TO BE 0.46 (0.018).

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	12.35	12.80	0.486	0.504
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LΕ	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
Q1	0.70	0.90	0.028	0.035
Z		0.81		0.032

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